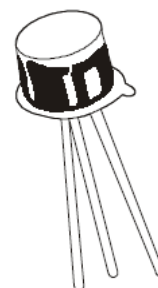


Small Signal General Purpose Transistor (PNP)

Features

- Switching and Linear Application
DC to VHF Amplifier Application
- RoHS Compliant



Mechanical Data

TO-18



Case:	TO-18, Metal can package
Terminals:	Solderable per MIL-STD-202, Method 208
Weight:	0.35 grams

Maximum Ratings ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	2N2907A	Unit
V_{CB0}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EB0}	Emitter-Base Voltage	5.0	V
I_C	Collector Current Continuous	600	mA
P_D	Power Dissipation at $T_A=25^{\circ}C$	400	mW
	Power Dissipation Derate above $T_A=25^{\circ}C$	2.28	mW/ $^{\circ}C$
	Power Dissipation at $T_C=25^{\circ}C$	1.8	W
	Power Dissipation Derate above $T_C=25^{\circ}C$	10.3	mW/ $^{\circ}C$
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-65 to +200	$^{\circ}C$

Small Signal General Purpose Transistor (PNP)

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Electrical Characteristics ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	Min.	Max.	Unit	Conditions
V_{CB0}	Collector-Base Voltage	60	-	V	I _C =10μA, I _E =0
*V_{CEO}	Collector-Emitter Voltage	60	-	V	I _C =10mA, I _B =0
V_{EB0}	Emitter-Base Voltage	5.0	-	V	I _E =10μA, I _C =0
h_{FE}	D.C. Current Gain	75	-		V _{CE} =10V, I _C =0.1mA
		100	-		V _{CE} =10V, I _C =1mA
		100	-		V _{CE} =10V, I _C =10mA
		100	300		*V _{CE} =10V, I _C =150mA
		50	-		*V _{CE} =10V, I _C =500mA
*V_{CE(sat)}	Collector-Emitter Saturation Voltage	-	0.4	V	I _C =150mA, I _B =15mA
		-	1.6	V	I _C =500mA, I _B =50mA
*V_{BE(sat)}	Base-Emitter Saturation Voltage	-	1.3	V	I _C =150mA, I _B =15mA
		-	2.6	V	I _C =500mA, I _B =50mA
I_{CBO}	Collector-Cut-off Current	-	10	nA	V _{CB} =50V, I _E =0
		-	10	μA	V _{CB} =50V, I _E =0, T _A =150° C
I_{CEX}	Collector-Cut-off Current	-	50	nA	V _{CE} =30V, V _{BE} =0.5V
I_B	Base Current	-	50	nA	V _{CE} =30V, V _{BE} =0.5V
**f_t	Transition Frequency	200	-	MHz	I _C =50mA, V _{CE} =20V, f=100MHz
C_{ob}	Out-Put Capacitance	-	8.0	pF	V _{CB} =10V, I _E =0, f=100KHz
C_{ib}	In-Put Capacitance	-	30	pF	V _{BE} =2V, I _C =0, f=100KHz
t_d	Delay Time	-	10	nS	I _C =150mA, I _{B1} =15mA
t_r	Rise Time	-	40	nS	V _{CC} =30V
t_{on}	Turn-On Time	-	45	nS	
t_s	Storage Time	-	80	nS	I _C =150mA, I _{B1} =I _{B2} =15mA
t_f	Fall Time	-	30	nS	V _{CC} =6V
t_{off}	Turn-Off Time	-	100	nS	

*Pulse Test: -Pulse Width=300μs, Duty Cycle=2%

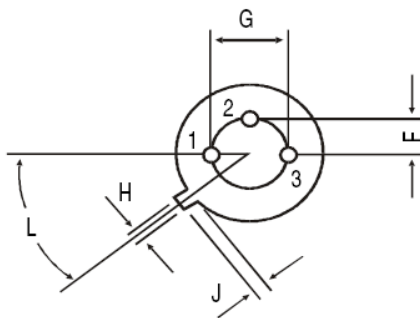
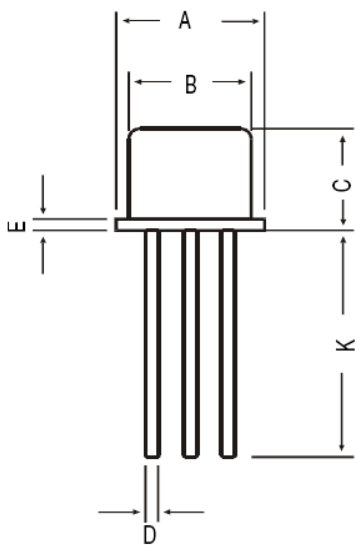
Small Signal General Purpose Transistor (PNP)

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**ft is defined as the frequency at which h_{fe} extrapolates to unity

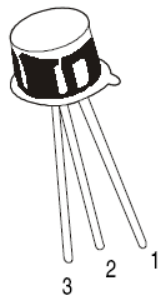
Dimensions in mm

TO-18



All dimensions in mm.

DIM	MIN	MAX
A	5.24	5.84
B	4.52	4.97
C	4.31	5.33
D	0.40	0.53
E	—	0.76
F	—	1.27
G	—	2.97
H	0.91	1.17
J	0.71	1.21
K	12.70	—
L	45 DEG	



PIN CONFIGURATION

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR

Packing Information:

Standard Pack	
Details	Net Weight/Qty.
1k/polybag	350gm/1k pcs

Small Signal General Purpose Transistor (PNP)

2N2907A

Carton Information:

Inner Carton Box	
Size	Qty.
3' x 7.5' x 7.5'	5k pcs

Outer Carton Box		
Size	Qty.	Gross Weight
17' x 15' x 13.5'	80k pcs	34kgs

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